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(54) **DISPLAY DEVICE HAVING
COUNTER-TWISTING LIQUID CRYSTAL
AREAS AND METHOD OF OPERATING AND
MANUFACTURING THE SAME**

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(57) **ABSTRACT**

A display apparatus, includes: a first substrate; a gate line formed over the first substrate; a data line traversing the gate line, and comprising a source electrode; a drain electrode facing the source electrode to define a channel area; a passivation layer formed over the data line and the drain electrode, and comprising an organic material; a pixel electrode formed over the passivation layer, and comprising a first stem electrode, at least a part of which is overlapped with the gate line or the data line, and a plurality of first branch electrodes contacted to the first stem electrode where one set of the first branch electrodes extend longitudinally in a direction different from the longitudinal extension direction of another set of the first branch electrodes so as to thereby cause opposed twisting of corresponding liquid crystal material.

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(30) **Aug. 10, 2006 (KR) 10-2006-0075843**

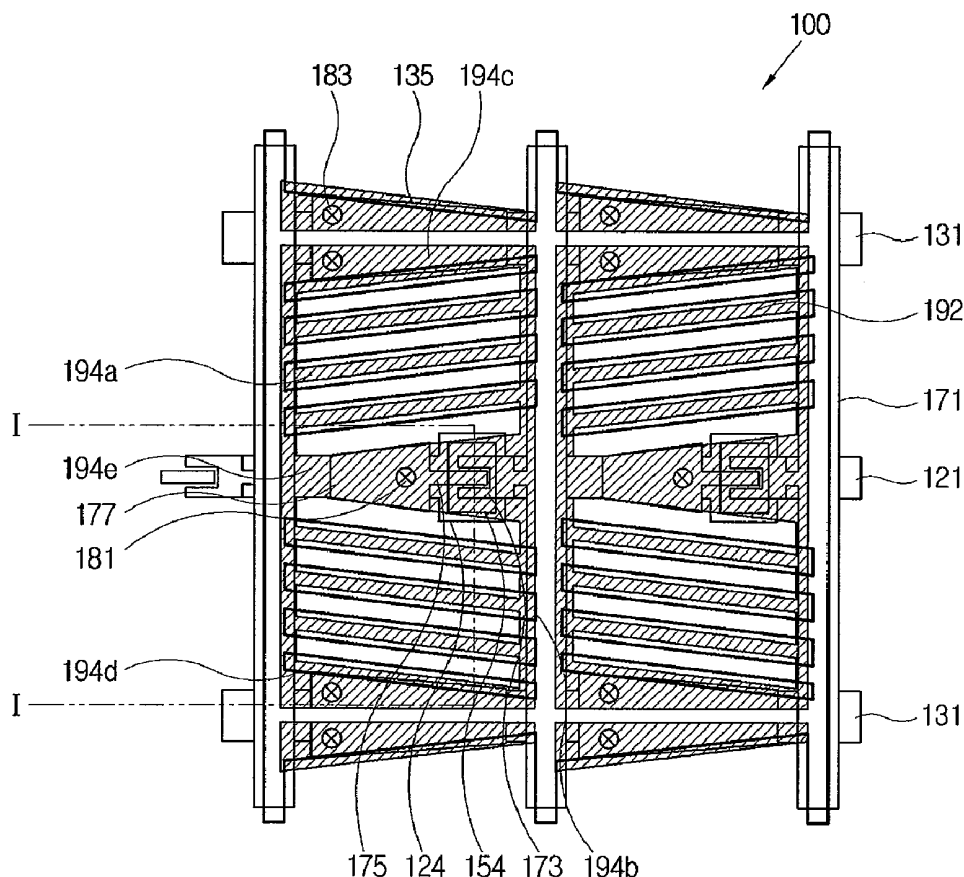


FIG. 1

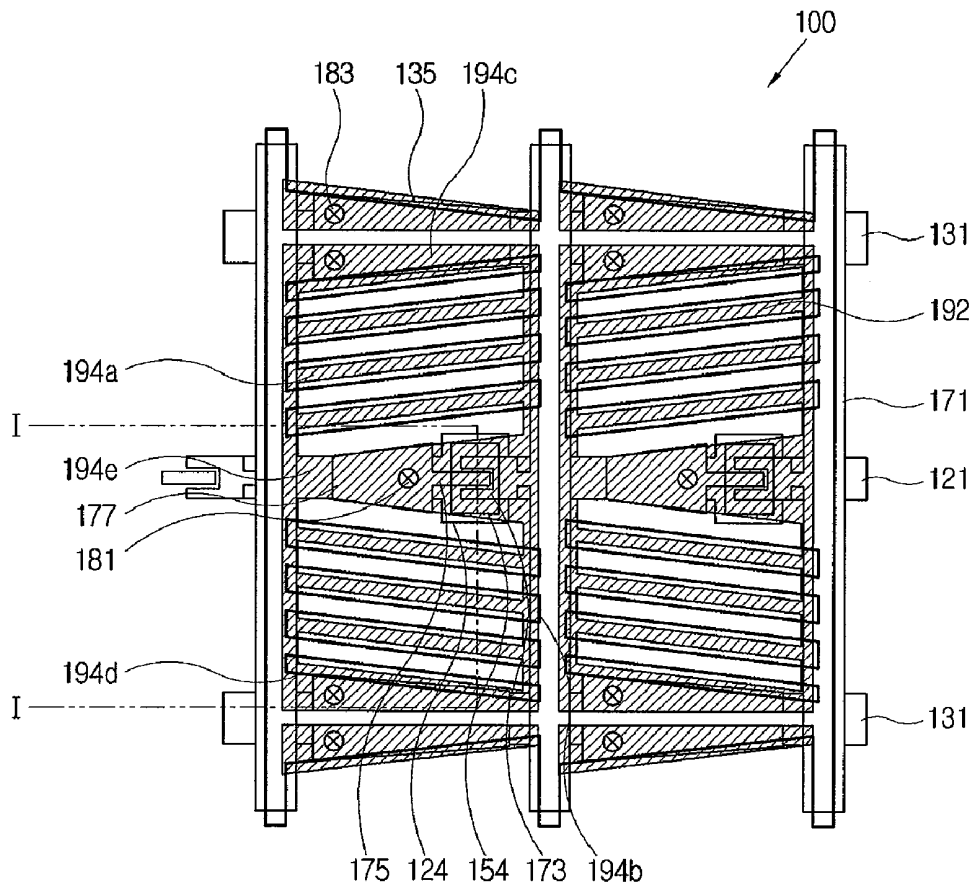


FIG. 2

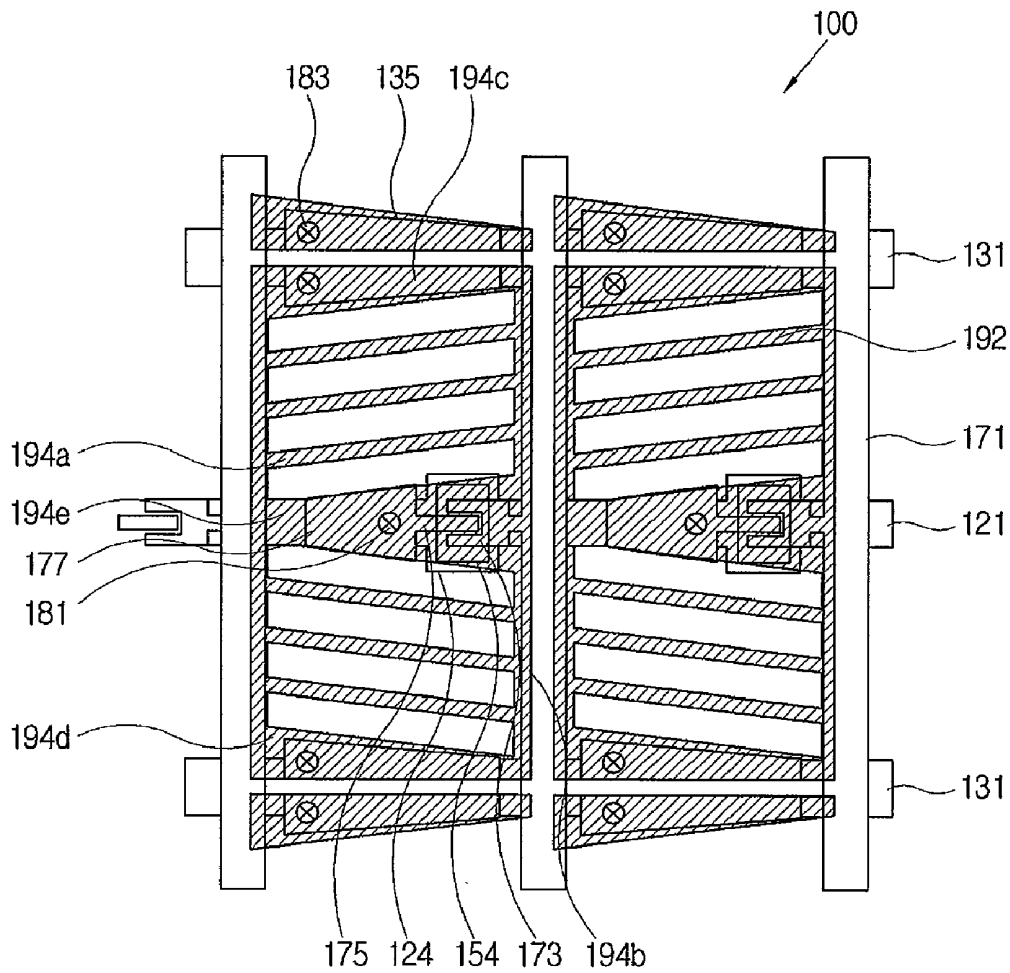


FIG. 3

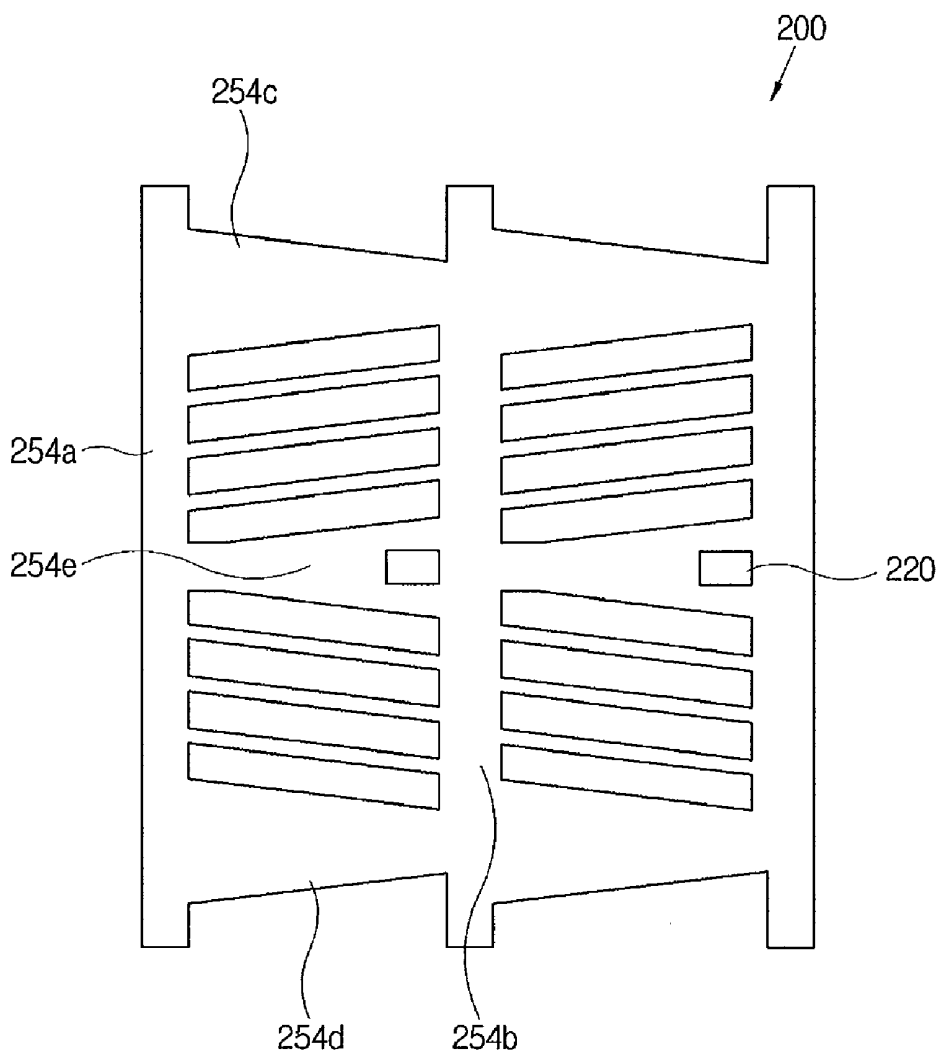


FIG. 4

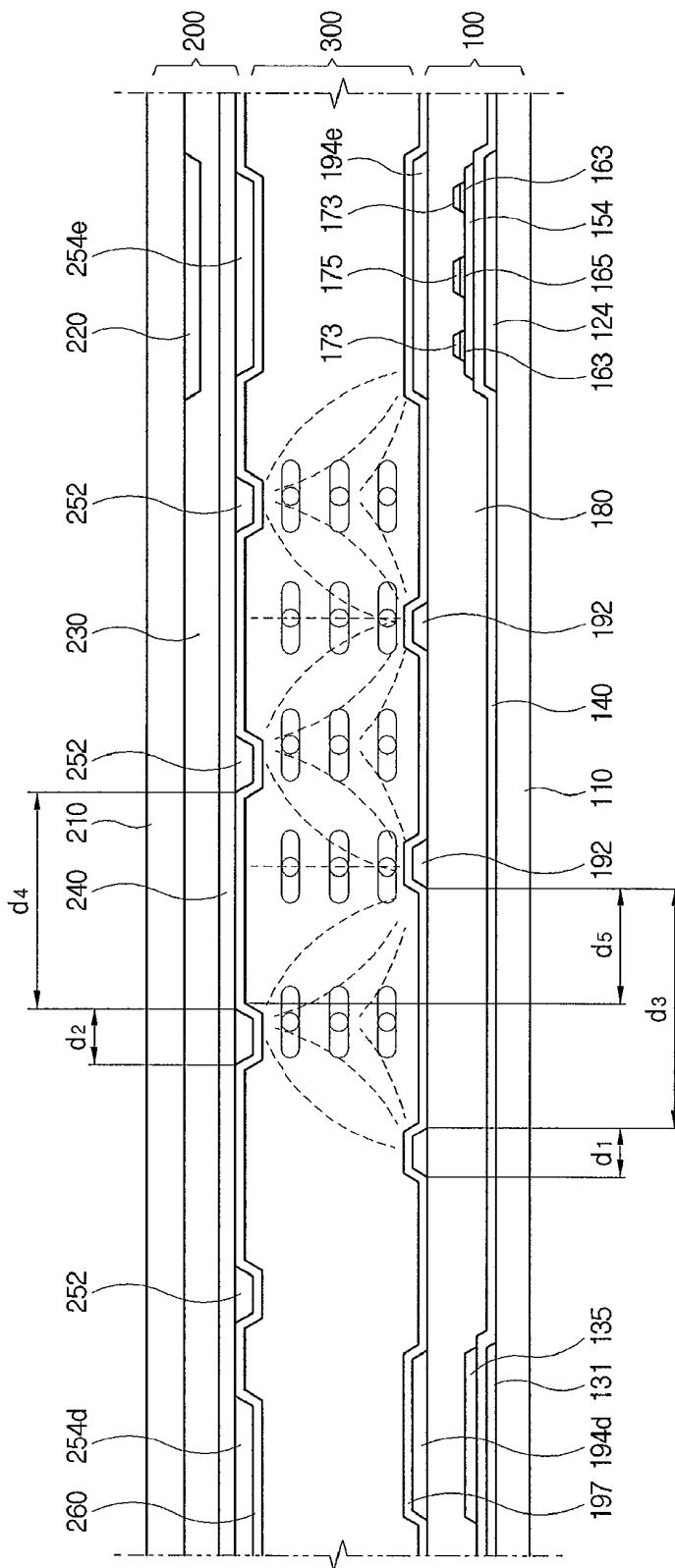


FIG. 5

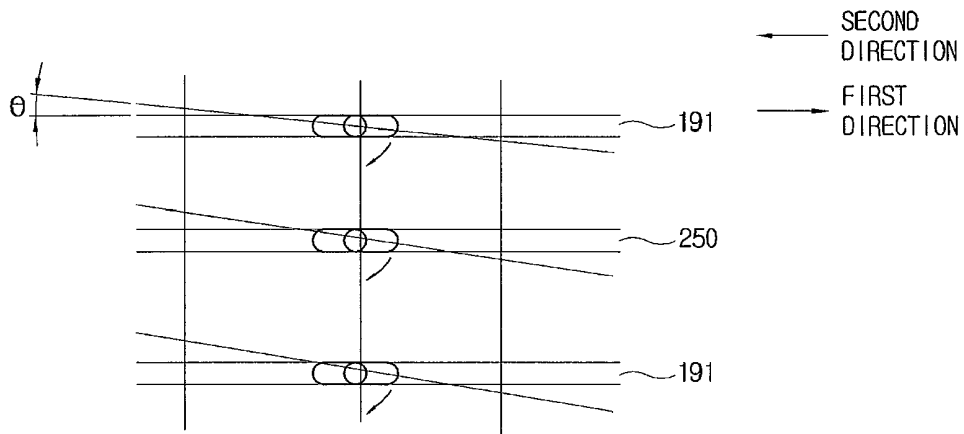


FIG. 6

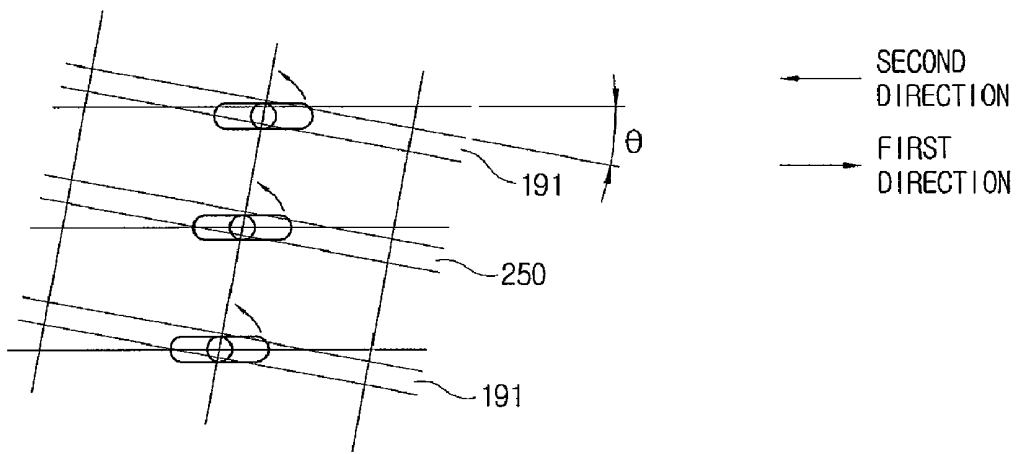


FIG. 7

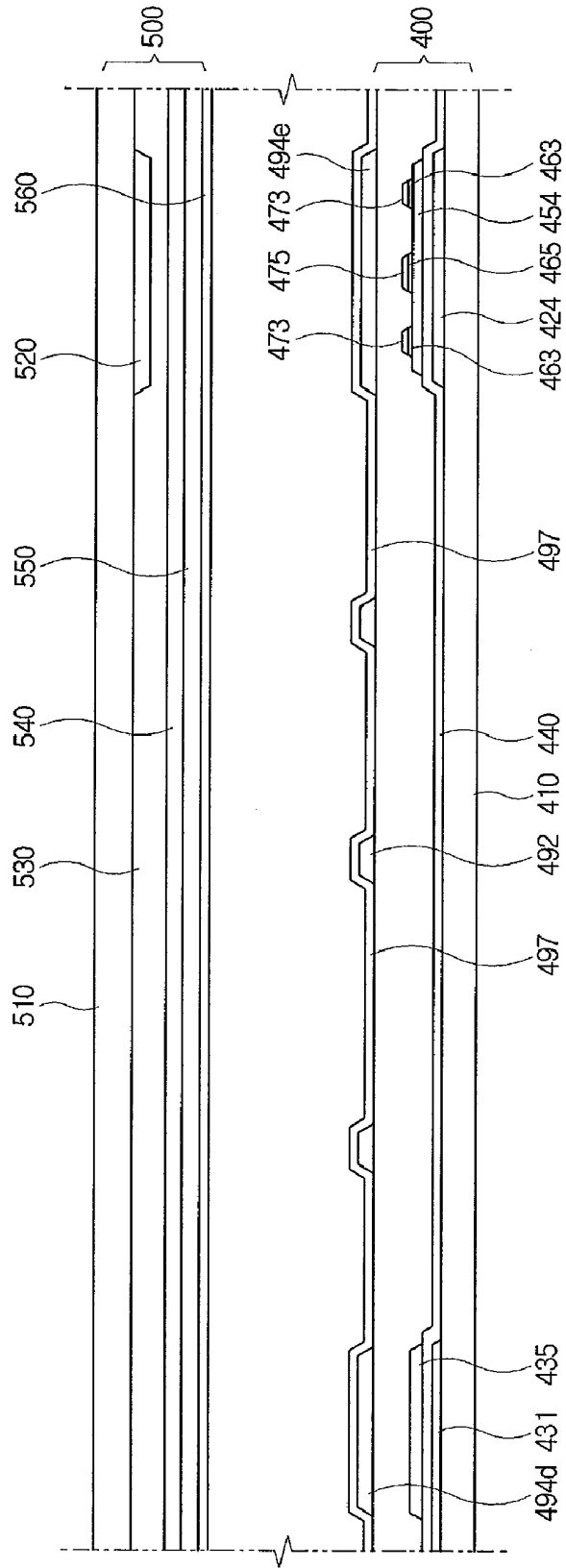


FIG. 8

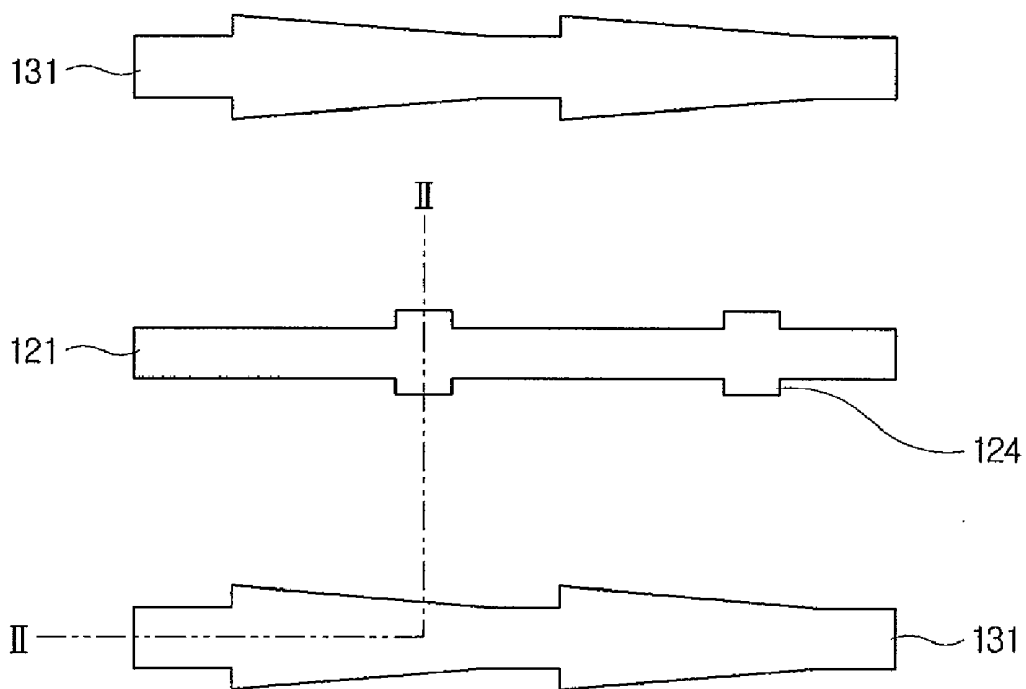


FIG. 9

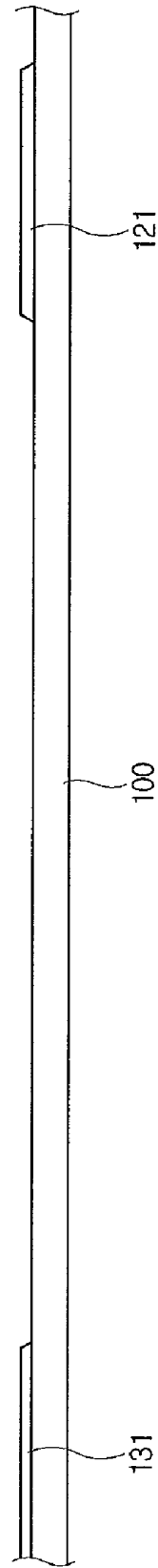


FIG. 10

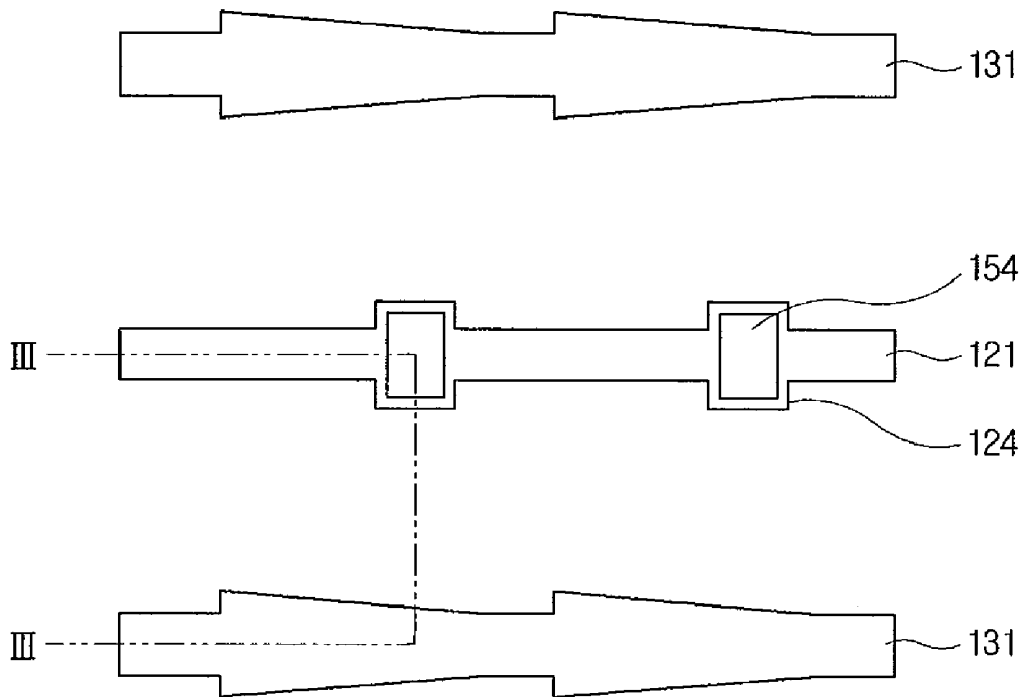


FIG. 11

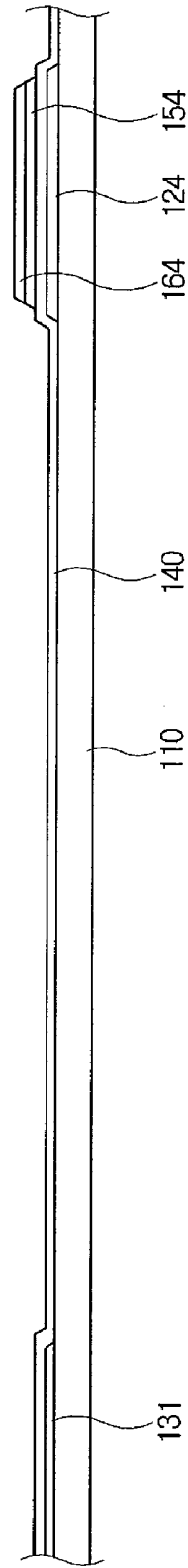


FIG. 12

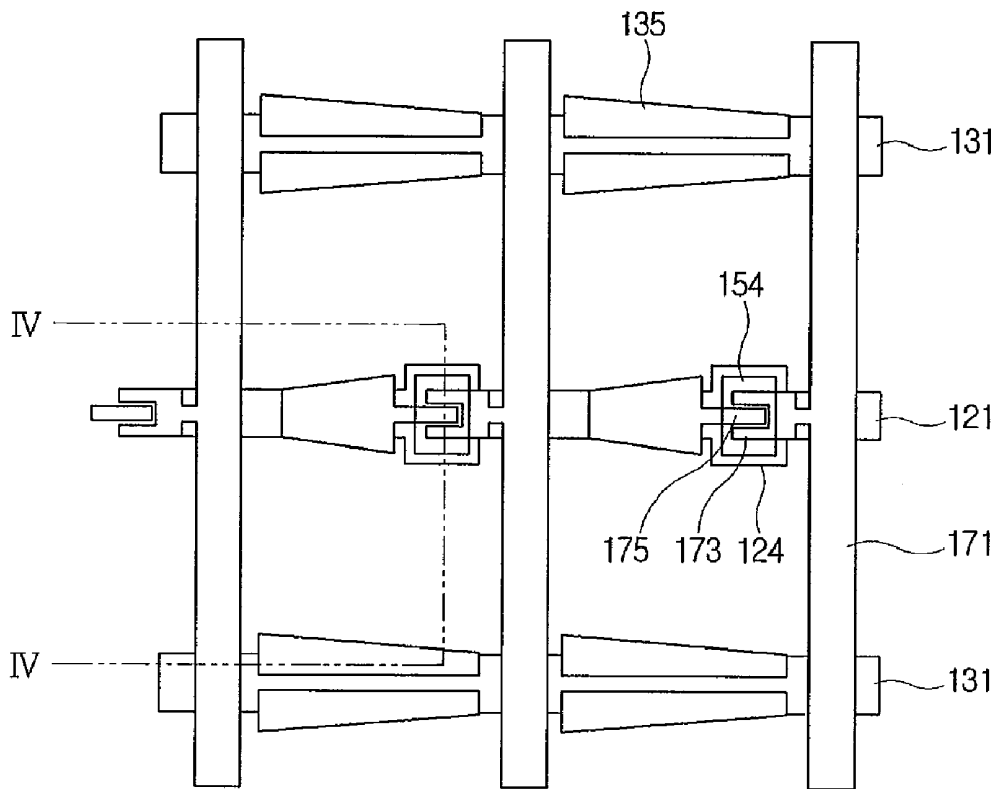


FIG. 13

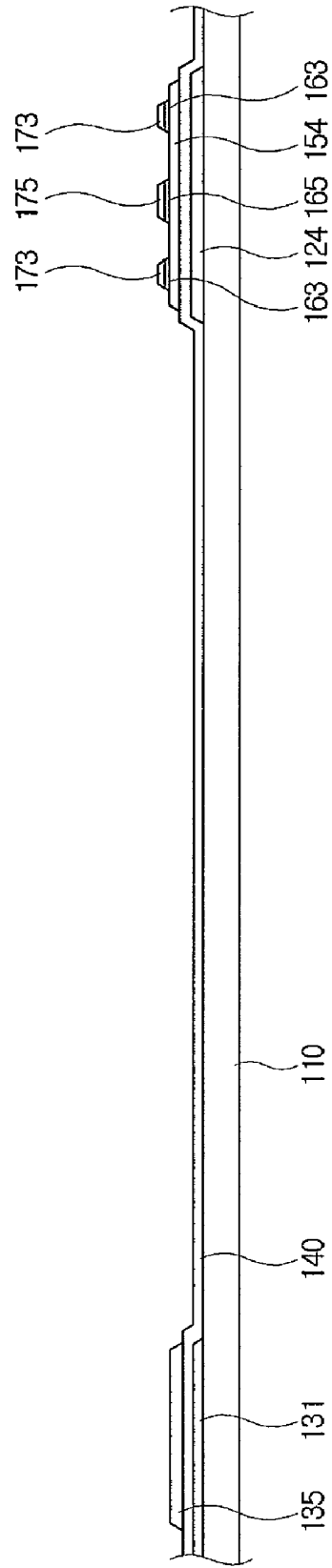


FIG. 14

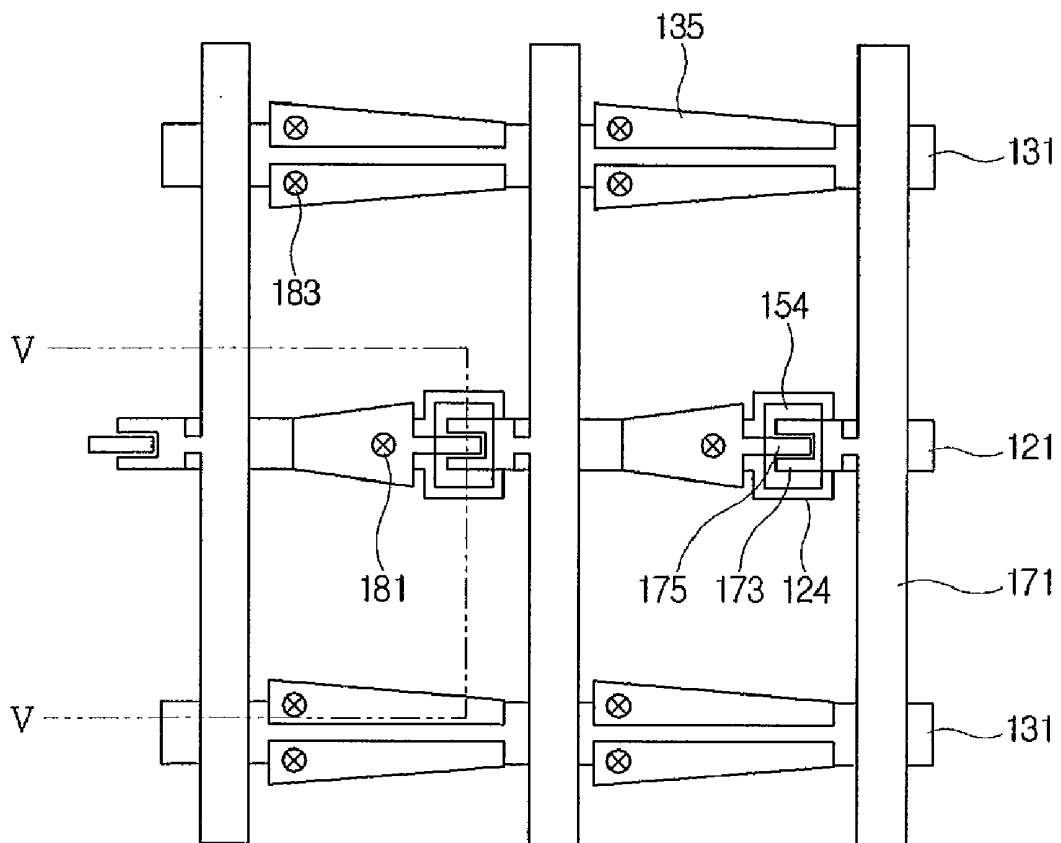


FIG. 15

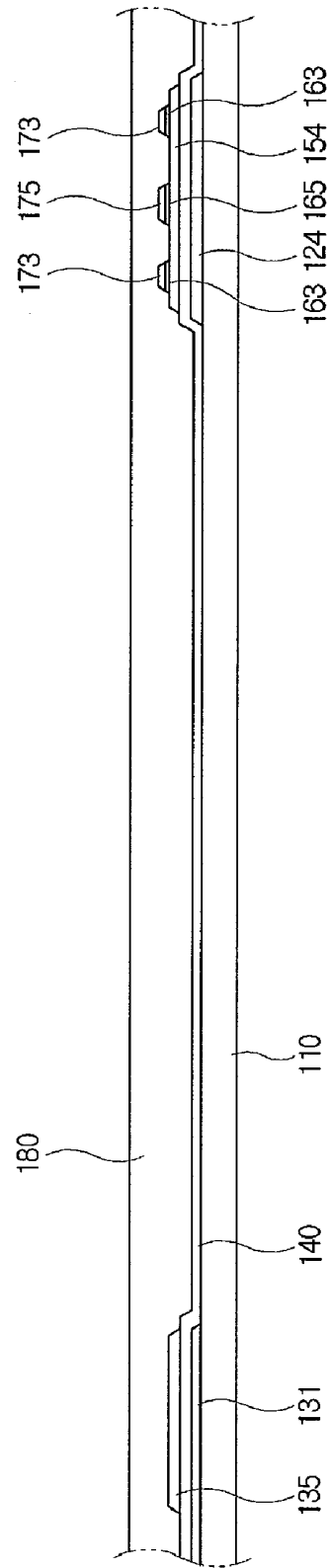


FIG. 16

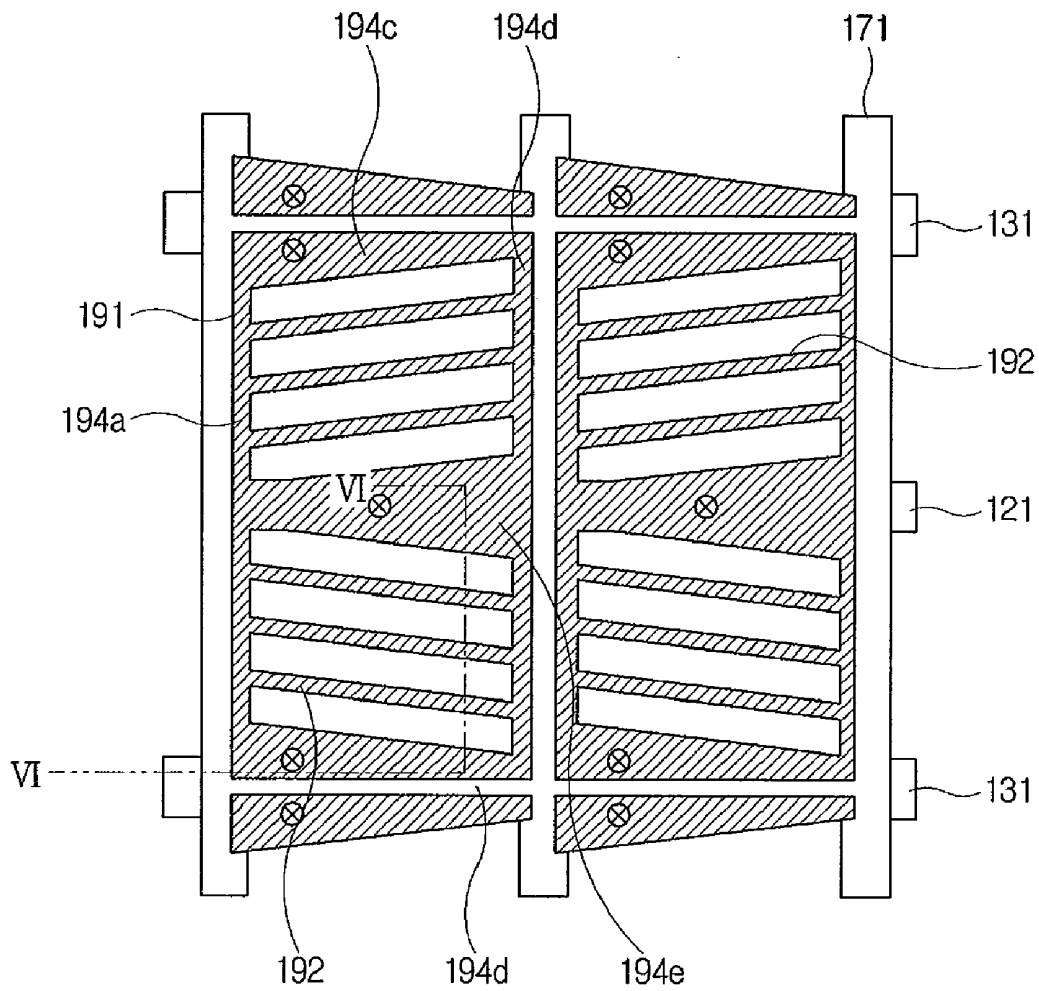
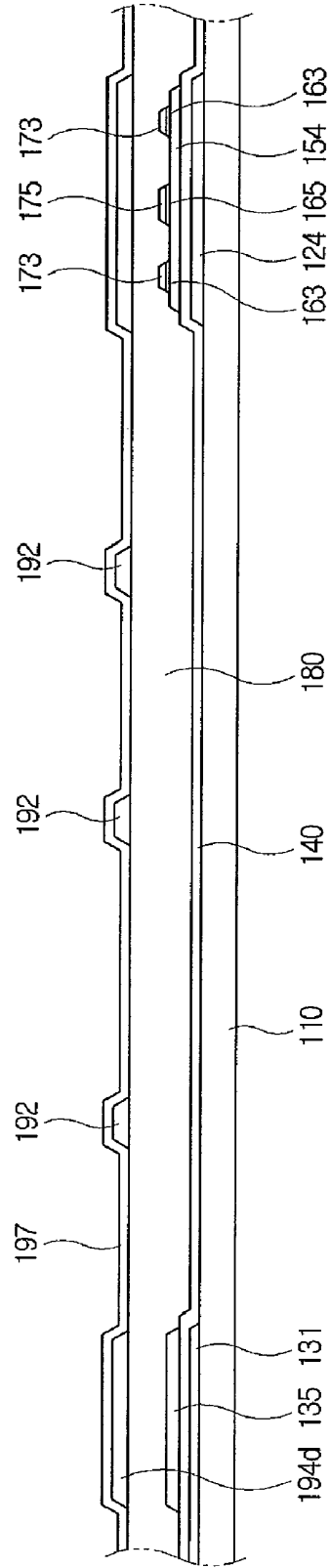


FIG. 17



**DISPLAY DEVICE HAVING
COUNTER-TWISTING LIQUID CRYSTAL
AREAS AND METHOD OF OPERATING AND
MANUFACTURING THE SAME**

CROSS-REFERENCE TO RELATED
APPLICATIONS

[0001] This application claims priority from Korean Patent Application No. 2006-0075843, filed on Aug. 10, 2006, in the Korean Intellectual Property Office, the disclosure of which is incorporated herein by reference.

BACKGROUND

[0002] 1. Field of Invention

[0003] Apparatuses and methods consistent with the present disclosure of invention relate to Liquid Crystal Display (LCD) devices and manufacturing methods therefor.

[0004] 2. Description of Related Art

[0005] Generally, a liquid crystal display device is one of the most popular flat panel displays used for computer monitor applications and the like. An LCD device typically includes two display substrates formed as a sandwich with liquid crystal material interposed therebetween. Inwardly facing surfaces of the two display substrates have electric field generating electrodes disposed on them such as an array of pixel electrodes and a common electrode, and the liquid crystal material is inserted between the two display substrates. The liquid crystal material has a dielectric anisotropy characteristic that allows it to alter transmission of light there-through as a function of an electric field applied across the material.

[0006] More specifically, the liquid crystal display device controls an alignment of liquid crystal molecules in the liquid crystal layer by supplying a control voltage between the field generating electrodes to thereby apply an electric field of desired intensity and/or polarity to the liquid crystal material to thereby effect a twisting of the liquid crystal material and to thus control polarization of light passing through the material, thereby displaying a desired image.

[0007] The twisted nematic (TN) type of liquid crystal material has been widely used. In the TN type of liquid crystal display, the field generating electrodes are disposed on the counterfacing inner surfaces of the two display substrates, respectively, and liquid crystal polarization directors are arranged in the device to encourage a normal twisting by 90° of light passing from the lower display substrate to the upper display substrate. This twisting in combination with polarization plates, prevents light from passing through, thus presenting a dark pixel area. Then, a twisting voltage is applied between the two field generating electrodes to change the normal liquid crystal polarization and allow light to pass through thus changing the dark pixel area into a lit one. However, the liquid crystal display device of this TN type tends to have a narrow viewing angle with poor image contrast when viewed from one side or another of the display rather than head on. Accordingly, a liquid crystal display of an IPS (in-plane switching) type or a PLS (plane to line switching) type has been developed as an alternative to the TN type.

[0008] However, in the conventional IPS type and the PLS type, since both of the two field generating electrodes are

disposed on a single display substrate, light transmittance and image visibility become deteriorated.

SUMMARY

[0009] The present disclosure provides a display device has improved visibility and transmittance. According to one aspect of the present disclosure, a display device is provided with an improved aperture ratio.

[0010] A method in accordance with the disclosure causes liquid crystal material of a same pixel area to twist in opposed directions (i.e., clockwise and counterclockwise) so as to provide improved image contrasting when the image is viewed from one side or another of the display rather than head on. Thus, visibility from different angles is improved.

[0011] In one embodiment, a display apparatus, comprises: a first substrate; a gate line formed over the first substrate; a data line traversing the gate line to define a pixel area, a pixel electrode formed in the pixel area to have electric field generating branch-electrodes extending in substantially different directions and a first stem-electrode joining the branch-electrodes together; a second substrate facing the first substrate; a common electrode formed over the second substrate, where the common electrode may comprise a plurality of second branch-electrodes overlapping the pixel area and extending in said substantially different directions where the second branch-electrodes are positioned to be interdigitated relative to the first branch-electrodes, and a second stem-electrode connecting the second branch-electrodes of the common electrode; and a liquid crystal layer interposed between the first substrate and the second substrate.

[0012] According to an exemplary embodiment, the display apparatus further comprises a first parallel alignment layer formed over the pixel electrode and rubbed in a first direction, and a second parallel alignment layer formed over the common electrode and rubbed in a second direction, wherein the first direction and the second direction substantially parallel each other, and are opposite to each other.

[0013] According to the exemplary embodiment, the first substrate further comprises a storage electrode for defining a storage capacitor, where at least a part of the storage electrode is overlapped with the pixel electrode.

[0014] According to the exemplary embodiment, the liquid crystal layer comprises a liquid crystal with a positive dielectric anisotropy, and the width of the first branch electrodes and the width of the second branch-electrodes are each smaller than about 6 μm. In one embodiment, an electrode gap between an upper set of first branch electrodes and a lower, differently directed set of first branch electrodes is about 20 μm to 40 μm.

[0015] According to another exemplary embodiment, the liquid crystal layer comprises a liquid crystal with a negative dielectric anisotropy, and the width of the first branch electrodes are each smaller than about 6 μm. In one such embodiment, an electrode gap between the upper first branch electrodes and the lower first branch electrodes is about 4 μm to 14 μm.

[0016] According to the exemplary embodiment, a lengthwise direction of rotation of the upper first branch electrodes has an angle of 0° to 30° clockwise with respect to a lengthwise direction of the gate line while the same angle is repeated counterclockwise for the lower first branch electrodes.

[0017] According to the exemplary embodiment, the upper and lower first branch electrodes are symmetrical with respect to the gate line.

[0018] Other aspects of the disclosure appear in the below detailed description.

BRIEF DESCRIPTION OF THE DRAWINGS

[0019] The above and/or other aspects of the present disclosure will become more readily appreciated from the following description of the exemplary embodiments, taken in conjunction with the accompanying drawings, in which:

[0020] FIG. 1 is an arrangement diagram illustrating a configuration of a liquid crystal display device according to a first exemplary embodiment;

[0021] FIG. 2 is an arrangement diagram illustrating a configuration of a thin film transistor (TFT)-supporting substrate of the liquid crystal display device in FIG. 1;

[0022] FIG. 3 is an arrangement diagram illustrating a configuration of a common electrode supporting substrate of the liquid crystal display device in FIG. 1;

[0023] FIG. 4 is a sectional view taken along line I-I in FIG. 1;

[0024] FIGS. 5 and 6 are sectional views illustrating arrangements of liquid crystal molecules in an operation of the liquid crystal display device according to the first exemplary embodiment;

[0025] FIG. 7 is a sectional view illustrating a configuration of a liquid crystal display device according to a second exemplary embodiment;

[0026] FIG. 8 is an arrangement diagram illustrating a first stage of a manufacturing method of a thin film transistor according to the first exemplary embodiment;

[0027] FIG. 9 is a sectional view taken along line II-II in FIG. 8;

[0028] FIG. 10 is an arrangement diagram illustrating a second stage following the first stage in FIGS. 8 and 9;

[0029] FIG. 11 is a sectional view taken along line III-III in FIG. 10;

[0030] FIG. 12 is an arrangement diagram illustrating a third stage following the second stage in FIGS. 10 and 11;

[0031] FIG. 13 is a sectional view taken along line IV-IV in FIG. 12;

[0032] FIG. 14 is an arrangement diagram illustrating a fourth stage following the third stage in FIGS. 12 and 13;

[0033] FIG. 15 is a sectional view taken along line V-V in FIG. 14;

[0034] FIG. 16 is an arrangement diagram illustrating a fifth stage following the fourth stage in FIGS. 14 and 15; and

[0035] FIG. 17 is a sectional view taken along line VI-VI in FIG. 16.

DETAILED DESCRIPTION

[0036] Reference will now be made in detail to exemplary embodiments in accordance with the present disclosure, where the examples are illustrated in the accompanying drawings, and wherein like reference numerals refer to like or similar elements throughout.

[0037] Hereinafter, a liquid crystal display device according to a first exemplary embodiment will be described by referring to FIGS. 1 to 4.

[0038] First, a thin film transistor (TFT) supporting substrate 100 having transparency will be described in detail by referring to FIGS. 1, 2 and 4.

[0039] The TFT-supporting substrate 100 comprises an insulating substrate 110 such as one made of a transparent glass and/or transparent plastics, and where a plurality of gate

lines (GL's) 121 and a plurality of first storage electrodes (ST's) 131 are formed over the electrically insulating and optically transparent substrate 110.

[0040] Each gate line 121 (only one shown) transmits a corresponding gate signal to the gate terminals (124) of a corresponding row of TFT's (i.e., field effect transistors—two shown in FIGS. 1-2), and extends mainly in a transverse direction in the illustration. The gate line 121 includes an end part (not shown) widened for connection with an outer driving circuit and further widened at parts disposed at respective openings of an adjacent dielectric for connections to a plurality of gate electrodes 124 by way of extensions protruding upward and through vias to reach the other layers for connections thereto.

[0041] A gate driving circuit (not shown) is provided for generating the gate signal and it may comprise an integrated circuit (IC) chip mounted on a flexible printed circuit film (not shown) attached to the insulating substrate 110, or directly mounted on the insulating substrate 110 itself. Alternatively, the gate driving circuit may be directly formed integrally on the insulating substrate 110. If the gate driving circuit is directly formed on the insulating substrate 110, the gate line 121 may extend to be directly connected to the gate driving circuit.

[0042] A first storage electrode 131 is defined to oppose another electrode 135 and to thereby define a storage capacitor. The first storage electrode 131 extends on the TFT-supporting substrate 100 parallel to the gate line 121, in the horizontal or transverse direction of the illustration. The first storage electrode 131 defines a boundary of a pixel area (PA) together with a corresponding data line 171. That is, the first storage electrode 131 is formed around an upper edge of the pixel areas shown in FIG. 2 for example (two horizontally adjacent PA's shown). The first storage electrode 131 is formed between a first pixel area and its vertically adjacent pixel area (not shown). At least a part of the first storage electrode 131 is overlapped with a pixel electrode 191. The gate line 121 extends into the pixel area. For example, the gate line 121 extends into and through a central part of the pixel area, and divides the pixel area into two subareas.

[0043] A side of the first storage electrode 131 has an inclined angle of 0° to 30° with respect to a lengthwise direction of the gate line 121. The first storage electrode 131 has a symmetrical configuration with respect to an imaginary central line paralleling the gate line 121. For example, the first storage electrode 131 may have a symmetric trapezoidal shape, for example that mirroring the illustrated shape of storage electrode 135 in combination with stem electrode 194c. (See also FIG. 8.) Since the first storage electrode 131 is overlapped with the pixel electrode 191 (not shown) at an edge of the pixel area, undesirable leakage of light around an edge of the pixel electrode 191 can be prevented without need for a separate light intercepting member (i.e., a black masking matrix).

[0044] The first storage electrode 131 may be formed of (patterned from) the same conductive material layer used for forming the gate line 121. Also, the first storage electrode 131 receives a predetermined voltage such as a common reference voltage.

[0045] The gate line 121 and the first storage electrode 131 may be composed of an aluminum-based metal such as aluminum, an aluminum alloy, etc., or a silver-based metal such as silver, a silver alloy, etc., or a copper-based metal such as copper, a copper alloy, etc., a molybdenum series metal such

as molybdenum, a molybdenum alloy, etc., and similarly for chrome, tantalum, titanium, etc.

[0046] The gate line **121** and the first storage electrode **131** may have a multi layer configuration comprising two conductive layers (not shown) with different physical properties. One of the conductive layers may comprise a metal having a relatively small resistivity such as an aluminum series metal, a silver series metal, a copper series metal, etc. to reduce a signal delay or a drop of voltage. The other of the conductive layers may comprise an interface material with a good physical, chemical and electrical contact properties relative to other materials, especially relative to ITO (indium tin oxide) and/or IZO (indium zinc oxide). The interface material may be one such as a molybdenum series metal, chrome, tantalum, titanium, etc. For example, a chrome lower layer and an aluminum (alloy) upper layer, and an aluminum (alloy) lower layer and a molybdenum (alloy) upper layer are applied thereto. However, the gate line **121** may comprise other various metals or electric conductors.

[0047] Over the gate line **121** and the first storage electrode **131**, a gate insulating layer **140** is provided and it includes a dielectric such as a silicon nitride SiN_x , a silicon oxide SiO_x or the like.

[0048] Over the gate insulating layer **140**, a plurality of semiconductor islands **154** are provided and these may include hydrogenated amorphous silicon (referred to 'a-Si'), polysilicon or the like. The semiconductor islands **154** of respective TFT's overlap the corresponding gate electrode **124** of those transistors.

[0049] A plurality of ohmic island contact members **163** and **165** are formed over the island semiconductors **154**. The ohmic island contact members **163** and **165** may comprise hydrogenated amorphous silicon densely doped as N+ with an n-type impurity such as phosphorus, or a silicide. The ohmic island contact members **163** and **165** are disposed to make a source/drain pair over the island semiconductors **154**.

[0050] The ohmic island contact members **163** and **165** are disposed only between the island semiconductors **154**, and the data line **171** and a drain electrode **175**, and reduce a contact resistance therebetween. The island semiconductors **154** between the source electrode **173** and the drain electrode **175** define a non-metalized channel region. Also, the island semiconductors **154** have an exposed part not covered by the data line **171** and the drain electrode **175**.

[0051] A plurality of data lines **171** and a plurality of drain electrodes **175** are formed over the ohmic island contact members **163** and **165** and the gate insulating layer **140**. A plurality of second storage electrodes **135** are formed over the first storage electrode **131** and the gate insulating layer **140**.

[0052] The data line **171** transmits a data signal, and extends mainly in a perpendicular direction to cross the gate line **121**. The data line **171** includes first and second end parts (not shown) widened for connection with an outer driving circuit and further parts for coupling with a plurality of source electrodes **173** protruding upward and other layers, or for connection thereto. A data driving circuit (not shown) generating the data signal may be mounted on a flexible printed circuit film (not shown) attached on the insulating substrate **110**, directly mounted on the insulating substrate **110** or directly integrated to the insulating substrate **110**. If the data driving circuit is directly integrated onto the insulating substrate **110**, the data line **171** may extend to be directly connected therewith.

[0053] The drain electrode **175** (see FIG. 4) is separated from the data line **171**, and also spaced-apart from the source electrode **173** while centering over the gate electrode **124** and the corresponding, channel region **154**. The drain electrode **175** includes a first end part **177** widened, and a second end part having a bar shape, and the second end part is surrounded by the source electrode **173** patterned in a U shape.

[0054] One gate electrode **124**, one source electrode **173** and one drain electrode **175**, together with the island semiconductor **154**, compose one TFT (thin film transistor), and a channel of the TFT is formed to the island semiconductor **154** between the source electrode **173** and the drain electrode **175**.

[0055] The second storage electrode **135** is formed in the same conductive material layer as that of the data line **171** and the drain electrode **175**, and may include the same material as the data line **171** and the drain electrode **175**. The second storage electrode **135** extends in a traverse direction to parallel the gate line **121**, and is formed to an edge of a pixel area. The second storage electrode **135** according to the first exemplary embodiment of the present invention may be overlapped with the first storage electrode **131**, and have the shape of an asymmetric half of a symmetrical trapezoid. A storage capacitance is formed in the region where the second storage electrode **135** and the first storage electrode **131** are overlapped with each other. Also, a storage capacitance may be further formed partially in the region where the second storage electrode **135** and the pixel electrode **191** are overlapped with each other.

[0056] In one embodiment, the data line **171**, the drain electrode **175** and the second storage electrode **135** are fabricated so as to include a refractory metal such as molybdenum, chrome, tantalum and titanium, or alloys thereof, and to have a multi layer configuration comprising a refractory metal layer (not shown) and a conductive layer (not shown) of a smaller resistance. For example, a double layer including a chrome or a molybdenum (alloy) lower layer and an aluminum (alloy) upper layer, and a triple layer including a molybdenum (alloy) lower layer, an aluminum (alloy) middle layer and a molybdenum (alloy) upper layer are applied thereto. However, the data line **171**, the drain line **175** and the second storage electrode **135** may include other various metals or electric conductors.

[0057] A passivation layer **180** (FIG. 4) is formed over the data line **171**, the drain electrode **175**, the second storage electrode **135** and the exposed part of the island semiconductor **154**. The passivation layer **180** may include an organic insulating material with a relatively moderate dielectric constant, and have photo sensitivity. For example, the passivation layer **180** includes an organic insulating material of acryl series, and dielectric constant thereof may be 3 to 5. The dielectric constant thereof may be 3.4 to 4. Also, the passivation layer **180** has a thickness of approximately 2.5 μm to 5 μm . Alternatively, the passivation layer **180** has a thickness of approximately 3 μm .

[0058] Since the passivation layer **180** comprising an organic material over the data line **171** has a relatively small or moderate dielectric constant and is capable of being thickened, the data line **171** and the pixel electrode **191** can be sufficiently insulated from each other. Accordingly, interference between the data line **171** and the pixel electrode **191** can be reduced so that the pixel electrode **191** may be overlapped with the data line **171** or the gate line **121** rather than being forced to terminate at the position where the data line **171** or

the gate line **121** begins. Accordingly, an aperture ratio can be improved because users can view a larger area of pixel electrode.

[0059] The passivation layer **180** may have a double layer configuration including an inorganic lower layer and an organic upper layer to prevent damage to the exposed part of the island semiconductor **154** with maintaining an excellent insulating property which an organic layer has. The inorganic lower layer may comprise silicon nitride SiN_x or silicon oxide SiO_x.

[0060] A plurality of contact holes **181** and **183** are formed through the passivation layer **180** to respectively expose the drain electrode **175** and the second storage electrode **135**, and a contact hole (not shown) is formed through the passivation layer **180** to expose an end part (not shown) of the data line **171**. Also, a plurality of contact holes (not shown) are formed through the passivation layer **180** and the gate insulating layer **140** to expose an end part (not shown) of the gate line **121**. The contact hole **181** exposing the drain electrode **175** and the contact hole **183** exposing the second storage electrode **135** are electrically connected to the pixel electrode **191**.

[0061] A plurality of pixel electrodes **191** are formed over the passivation layer **180**. The pixel electrodes **191** may include a transparent conductive material such as ITO (indium tin oxide), IZO (indium zinc oxide) or the like.

[0062] The pixel electrode **191** includes a plurality of first branch electrodes **192** each having a predetermined angle to a lengthwise direction of the gate line **121**. The plurality of first branch electrodes **192** are substantially parallel one another. Also, the pixel electrode **191** includes a plurality of first stem electrodes **194** contacting the plurality of first branch electrode **192**.

[0063] The plurality of first branch electrodes **192** in a first exemplary embodiment have a symmetrical configuration with respect to the gate line **121** formed to a central part of the pixel area to be divided into an upper first branch electrode **192** and a lower first branch electrode **192'**. A lengthwise direction of the first branch electrode **192** according to the first exemplary embodiment of the present invention may have an inclined angle of 0° to 30° with respect to a lengthwise direction of the gate line **121**. The width of the first branch electrode **192** may be smaller than 6 μm. In one embodiment, the width of the first branch electrode **192** is about 4 μm. An electrode gap between the first branch electrode **192** and the first branch electrode **192** may be 20 μm to 40 μm. For example, the electrode gap therebetween may be 31 μm.

[0064] The first stem electrodes **194** connect the upper first branch electrodes **192** and the lower first branch electrodes **192'**. The first stem electrode **194** according to the first exemplary embodiment includes a first part **194a**, a second part **194b**, a third part **194c**, a fourth part **194d** and a fifth part **194e**. The first and the second parts **194a** and **194b** are respectively formed at edges of the pixel area, and parallel the data line **171**. The first and the second parts **194a** and **194b** are overlapped with the data line **171**. The third and the fourth parts **194c** and **194d** are respectively formed at edges of the pixel area, and include a first side paralleling the gate line **121** and a second side having a predetermined inclined angle with respect to a lengthwise direction of the gate line **121**. For example, the third part **194c** includes a side having an angle of 0° to 30° with respect to a lengthwise direction of the gate line **121**, and the fourth part **194d** includes a side having an angle of 0° to 30° with respect to a lengthwise direction of the gate

line **121**. The third and the fourth parts **194c** and **194d** are overlapped with the gate line **121** and the second storage electrode **135**. The fifth part **194e** is formed to a central part of the pixel area, and includes a first side paralleling the upper first branch electrode **192**, and a second side paralleling the lower first branch electrode **192**. The fifth part **194e** may have a symmetric trapezoid shape.

[0065] Each pixel electrode **191** is physically and electrically connected with the drain electrode **175** of its corresponding TFT through the contact hole **181**, and receives the charge from the drain electrode **175** so as to attain a desired voltage level relative to the common electrode. Also, the pixel electrode **191** fills the contact hole **183** exposing the second storage electrode **135** and supplies charge to the second storage electrode **135**.

[0066] A first liquid crystal aligning layer **197** is formed over the pixel electrode **191**. This alignment layer **197** according to the first exemplary embodiment may comprise a parallel type of liquid crystal aligning layer.

[0067] Hereinafter, a common electrode supporting substrate **200** will be described by referring to FIGS. **1**, **3** and **4**.

[0068] As shown therein (see FIG. **4**), the common electrode supporting substrate **200** includes an electrically-insulating and optically transparent substrate **210** composed of a transparent glass and/or transparent plastics or the like.

[0069] A light intercepting member **220** is formed over the insulating substrate **210**. The light intercepting member **220** intercepts light leaking from the pixel area, and may include a first part corresponding to the gate line **121** or the data line **171**, and a second part corresponding to a thin film transistor.

[0070] The light intercepting member **220** according to the first exemplary embodiment may be an island type corresponding to the thin film transistor. Accordingly, the data line **171** and the first storage electrode **131** can prevent a light leakage by applying an organic layer to the passivation layer **180** and superposing the pixel electrode **191** over the data line **171** and the first storage electrode **131**. The shape of the light intercepting member **220** may be changed as deemed appropriate. Also, the light intercepting member **220** may be formed over the thin film transistor substrate **100**. Here, the light intercepting member **220** may be formed to a layer between the passivation layer **180** and the pixel electrode **191**, and may be provided to be an island type to cover the thin film transistor comprising the island semiconductor **154**, the source electrode **173** and the drain electrode **175**.

[0071] The common electrode supporting substrate **200** includes a plurality of color filters **230** and a planarizing layer **240**. The color filter **230** includes one of primary colors of red, green and blue, and may extend in a vertical direction. The color filter **230** may be formed over the thin film transistor display substrate **100**.

[0072] The planarizing layer **240** may include a (organic) insulating material, and prevents the color filter **230** from being exposed and supplies a planar surface. The planarizing layer **240** may be omitted if desired.

[0073] A common electrode **250** is formed over the planarizing layer **240**. The common electrode **250** may include a transparent conductive material such as ITO, IZO, etc. The common electrode **250** (FIG. **3**) includes a plurality of second branch electrodes **252** formed between the first branch electrodes **192** of the pixel electrode **191**, and not overlapped with the first branch electrodes **192** of the pixel electrode **191**. The second branch electrodes **252** may substantially parallel each

other, and may substantially parallel the branch electrodes 192 of the pixel electrode 191.

[0074] The second branch electrodes 252 according to the first exemplary embodiment have a symmetrical configuration with respect to the gate line 121 formed to a central part of the pixel area to be divided into an upper second branch electrode 252 and a lower second branch electrode 252. A lengthwise direction of the second branch electrode 252 has an angle of 0° to 30° with respect to a lengthwise direction of the gate line 121. The width of the second branch electrode 252 may be smaller than $6\ \mu\text{m}$. In one embodiment, the width of the second branch electrode 252 may be about $4\ \mu\text{m}$. An electrode gap between the second branch electrodes 252 may be $20\ \mu\text{m}$ to $40\ \mu\text{m}$. For example, the electrode gap between the second branch electrodes 252 may be $31\ \mu\text{m}$.

[0075] According to the first exemplary embodiment, the width of each of the first branch electrodes 192 (d_1) and the width of each of the second branch electrodes 252 (d_2) may be respectively about $4\ \mu\text{m}$, the electrode-to-electrode gap (d_3 , d_4) between each of the first branch electrodes 192 may be about $31\ \mu\text{m}$ and the electrode-to-electrode gap between each of the first branch electrodes 192 may be about $31\ \mu\text{m}$. Here, the second branch electrodes 252 may be formed between (interdigitated relative to) the first branch electrodes 192. Accordingly, a horizontal electrode-to-electrode gap (d_5) between one of the first branch electrodes 192 and the corresponding second branch electrode 252 may be about $13.5\ \mu\text{m}$. An opening 253 is formed between the second branch electrode 252 and the second branch electrode 252. The opening 253 may have a parallelogram shape, and a plurality of openings 253 parallel one another.

[0076] The common electrode 250 (FIG. 3) includes a second stem electrode 254 connecting the upper second branch electrodes 252 and the lower second branch electrodes 252'. Since a single layer excluding the opening part 253 is used as the common electrode 250, all remaining part of the common electrode 250 except the opening 253 and the second branch electrode 252 may define the second stem electrode 254.

[0077] The second stem electrode 254 according to the first exemplary embodiment includes a first part 254a, a second part 254b, a third part 254c, a fourth part 254d and a fifth part 254e. The first and the second parts 254a and 254b parallel the data line 171, and are overlapped with the data line 171. The third and the fourth parts 254c and 254d have shapes similar to the first storage electrode 131, and are overlapped with the first storage electrode 131. The fifth part 254e is formed to a central part of the pixel area, and includes a first side paralleling an upper area of the second branch electrode 252, and a second side paralleling a lower part of the second branch electrode 252. The fifth part 254e may have a trapezoid shape, and is overlapped with the second storage electrode 135.

[0078] The common electrode 250 receives a common reference voltage from the outside.

[0079] An upper liquid crystal aligning layer 260 is formed over the common voltage 250. The alignment layer 260 according to the first exemplary embodiment may comprise a parallel type alignment layer.

[0080] Hereinafter, an operation of a display device according to the first exemplary embodiment will be described by referring to FIGS. 1, 4, 5 and 6. FIGS. 5 and 6 are sectional views illustrating arrangements of liquid crystal molecules when a liquid crystal display device according to the first exemplary embodiment is operated.

[0081] The pixel electrode 191 receiving a data voltage generates an electric field together with the common electrode 250 receiving a common voltage, and determines a direction of orientation of liquid crystal molecules of the liquid crystal layer 300 positioned between both electrodes 191 and 250. Polarization of light transmitted through the liquid crystal layer 300 varies depending on the direction of orientation of the liquid crystal molecules.

[0082] The liquid crystal molecules of the liquid crystal display device according to the first exemplary embodiment have positive dielectric anisotropy. The alignment layer 197 of the thin film transistor display substrate 100 is rubbed in a first direction substantially paralleling the gate line 121, and the alignment layer 260 of the common electrode display substrate 200 is rubbed in a second direction paralleling the first direction and opposite to the first direction.

[0083] When a twisting voltage is not supplied, the liquid crystal molecules are aligned to be substantially parallel to surfaces of the substrates 110 and 210, and a major axis of the liquid crystal molecules substantially parallels the rubbed direction. The rubbed direction and the first branch electrodes 192 and the second branch electrodes 252 form a predetermined angle θ to each other as shown. Accordingly, the liquid crystal molecules are normally inclined at a predetermined first angle with respect to the first and the second branch electrodes 192 and 252 to have an initial twisted angle θ . The initial twisted angle is defined as an angle between the rubbed direction and a lengthwise direction of the branch electrodes, or an angle between the rubbed direction and the branch electrodes. The initial twisted angle is bigger than 0° , and equal to or smaller than about 30° .

[0084] Referring to FIG. 4, when a twisting voltage is supplied, an electric field is formed between the pixel electrode 191 and the common electrode 250. Flux lines of an electric field are formed between the first branch electrodes 192 of the pixel electrode 191 and the second branch electrodes 252 of the common electrode 250, and corresponding lateral field components and vertical field components are concurrently formed. Since the lateral field components prevail, the liquid crystal molecules rotate mainly on a plane paralleling the substrates to selectively display on and off states (light transmitting or not transmitting states or partial states in between).

[0085] An upper optical polarizing plate and a lower optical polarizing plate may be attached to the respective TFT and CE supporting substrates. Here, a transmission axis of the upper polarizing plate and a transmission axis of the lower polarizing plate may be perpendicular to each other. When a twisting voltage is not supplied, a polarizing direction of light transmitted through the liquid crystal is not changed by the liquid crystal material so that a dark state is displayed. When a twisting voltage is supplied, a polarizing direction of light transmitted through the liquid crystal is changed by the voltage-reoriented liquid crystal material so that a brightened state is displayed.

[0086] Referring to FIGS. 5 and 6, when a twisting voltage is supplied, liquid crystal molecules positioned to an area corresponding to the upper branch electrodes 192 and 252 rotate clockwise (FIG. 5) by the initial twisted angle, and liquid crystal molecules positioned to an area corresponding to the lower branch electrodes 192 and 252 rotate counterclockwise (FIG. 6) by the initial twisted angle. Accordingly, two side-by-side domains of light repolarization are formed, and visibility in a right-and-left direction can be improved.

[0087] Alternatively, liquid crystal molecules with a negative dielectric anisotropy may be used. Here, the liquid crystal molecules may be aligned in a vertical direction paralleling the data lines 171a and 171b. Also, the width of the first branch electrode 192 may be smaller than about 6 μm . The width of the first branch electrode 192 may be about 4 μm . Also, an electrode gap between the first branch electrode 192 and the first branch electrode 192 may be 4 μm to 14 μm , and may be 11 μm .

[0088] The width of the second branch electrode 252 may be smaller than 6 μm . In one embodiment, the width of the second branch electrode 252 is about 4 μm . Also, an electrode gap between the second branch electrode 252 and the second branch electrode 252 may be 4 μm to 14 μm . For example, the electrode gap therebetween may be 11 μm .

[0089] Alternatively, the width of the first branch electrode 192 and the width of the second branch electrode 252 may be respectively 4 μm and 4 μm , the electrode gap between the first branch electrode 192 and the first branch electrode 192 may be 11 μm , and the electrode gap between the second branch electrode 252 and the second branch electrode 252 may be 11 μm . Here, the second branch electrode 252 may be formed between the first branch electrodes 192. Accordingly, an electrode gap between the first branch electrode 192 and the second branch electrode 252 may be about 3.5 μm (equals 4.0 minus 0.5).

[0090] Hereinafter, a liquid crystal display device according to a second exemplary embodiment will be described by referring to FIG. 7.

[0091] FIG. 7 is a sectional view illustrating a configuration of a liquid crystal display device according to a second exemplary embodiment.

[0092] As shown in FIG. 7, a thin film transistor display substrate 400 of a liquid crystal display device according to a second exemplary embodiment has roughly the same configuration as the thin film transistor display substrate shown in FIGS. 1 to 6. However, the common electrode display substrate 500 according to the second exemplary embodiment has a different configuration. Hereinafter, a difference will be described.

[0093] The common electrode display substrate 500 includes an insulating substrate 510 including a transparent glass, plastics or the like. A light intercepting member 520 is formed to be an island type corresponding to a thin film transistor over the insulating substrate 510. The light intercepting member 520 may have various shapes as necessary. Also, the light intercepting member 520 may be formed over the thin film transistor display substrate 400. Here, the light intercepting member 520 may be formed to a layer between a passivation layer 480 and a pixel electrode 491, and may be provided to be an island type to cover the thin film transistor comprising a semiconductor 454, a source electrode 473 and a drain electrode 475.

[0094] The common electrode display substrate 200 includes a plurality of color filters 530 and a planarizing layer 540. The color filter 530 includes one of primary colors of red, green and blue, and may extend in a perpendicular direction. The color filter 530 may be formed over the thin film transistor display substrate 400.

[0095] A common electrode 550 is formed over the planarizing layer 540. The common electrode 550 according to the second exemplary embodiment of the present invention may be formed in a single planar shape without a pattern for forming an electric field. Accordingly, static electricity in the

liquid crystal display device can be discharged through the common electrode 550 having the planar shape, thereby reducing a static electricity strain because there are no points of peaked field intensity.

[0096] An electric gap, an electrode width and a rubbed direction of the liquid crystal display device according to the second exemplary embodiment may have the same configurations as the liquid crystal display device shown in FIGS. 1 to 6.

[0097] Hereinafter, a manufacturing method of a thin film transistor according to a first exemplary embodiment will be described by referring to FIGS. 8 to 17.

[0098] FIG. 8 is an arrangement diagram illustrating a first stage of a manufacturing method of a thin film transistor according to a first exemplary embodiment of FIG. 1 where FIG. 9 is a sectional view taken along line II-II in FIG. 8, FIG. 10 is an arrangement diagram illustrating a second stage following the first stage in FIGS. 8 and 9, FIG. 11 is a sectional view taken along line III-III in FIG. 10, FIG. 12 is an arrangement diagram illustrating a third stage following the second stage in FIGS. 10 and 11, FIG. 13 is a sectional view taken along line IV-IV in FIG. 12, FIG. 14 is an arrangement diagram illustrating a fourth stage following the third stage in FIGS. 12 and 13, FIG. 15 is a sectional view taken along line V-V in FIG. 14, FIG. 16 is an arrangement diagram illustrating a fifth stage following the fourth stage in FIGS. 14 and 15, and FIG. 17 is a sectional view taken along line VI-VI in FIG. 16.

[0099] First, referring to FIGS. 8 and 9, a conductive material layer is formed (i.e., blanket deposited) over the insulating substrate 110 including a transparent glass, plastics or the like. Then, a plurality of gate lines 121 including the gate electrode 124, and a plurality of first storage electrodes 131 are lithographically formed by patterning with a dry etching method and/or a wet etching method.

[0100] The gate line 121 includes a metal layer, and may include a single layer or multi layers.

[0101] Then, referring to FIGS. 10 and 11, the gate insulating layer 140 including silicon nitride SiN_x , an amorphous silicon (a-Si) layer (not shown), and a doped amorphous silicon layer (not shown) are formed over the gate line 121 and the first storage electrode 131. Then, the semiconductor 154 and the ohmic contact layer 164 are formed by dry-etching or wet-etching the amorphous silicon (a-Si) layer and the doped amorphous silicon layer

[0102] Then, referring to FIGS. 12 and 13, a conductive layer is formed over the gate insulating layer 140 and the ohmic contact layer 164. Then, the data line 171 including the source electrode 173, the drain electrode 175 and the second storage electrode 135 are formed by dry-etching or wet-etching the conductive layer. Then, the ohmic contact layer 164 is patterned under the mask of the source electrode 173 and the drain electrode 175 to form the ohmic contact member 163 and 164. Accordingly, the semiconductor 154 is exposed between the source electrode 173 and the drain electrode 175, and the channel area is formed.

[0103] Then, referring to FIGS. 14 and 15, an organic insulating layer is coated over all surface of the substrate by a slit coating method or a spin coating method to form the passivation layer 180. Alternatively, to protect the exposed semiconductor 154, an inorganic insulating layer comprising silicon nitride SiN_x may be deposited over all surface of the substrate by a chemical vapor deposition (CVD) before the

organic insulating layer is formed. Then, a plurality of contact holes **181** and **183** are formed by etching the passivation layer **180** by a photo process.

[0104] Then, referring to FIGS. **16** and **17**, a transparent conductive material such as ITO or IZO is deposited over the passivation layer **180** by a sputtering method, and then is patterned to form the pixel electrode **191**. Here, the contact hole **181** on the drain electrode **175** is filled with the transparent conductive material to electrically connect the drain electrode **175** and the pixel electrode **191**. Also, the contact hole **183** on the second storage electrode **135** is filled with the transparent conductive material to electrically connect the second storage electrode **135** and the pixel electrode **191**. Then, the alignment layer is formed over the pixel electrode **191**. Then, the alignment layer is rubbed in the first direction substantially paralleling the gate line **121**.

[0105] The common electrode display substrate may be manufactured by a following method.

[0106] A light intercepting member is formed over an insulating substrate including a transparent glass and/or transparent plastic or the like. The light intercepting member may be formed in an island type corresponding to the thin film transistor.

[0107] The color filter having red, green and/or blue coloration attributes for example is formed over the light intercepting member. After coating the substrate with a photo sensitive material comprising dyes or pigment over, the photo sensitive material is patterned by a photo-lithography process to form the color filter. For example, a red color filter material is laminated over all substrate, and is exposed and developed to form a red color filter. A green color filter and a blue color filter are formed by the same method.

[0108] Then, the planarizing layer is further formed over the color filter. An (organic) insulating material is laminated over all substrate formed with the color filter to form the planarizing layer.

[0109] Then, the common electrode is formed over the planarizing layer. A transparent conductive material such as ITO or IZO is deposited over all substrate by a sputtering method, etc., and then is patterned to form the common electrode by a photo etching method. If the common electrode without a pattern for forming an electric field is formed, the patterning process may be unnecessary.

[0110] Then, the alignment layer is formed. Then, alignment layer is rubbed in the second direction paralleling the first direction and opposite thereto.

[0111] As described above, the embodiments provide a liquid crystal display device employing an organic insulating layer for a passivation layer, and overlapping a pixel electrode with a data line, thereby improving the aperture ratio.

[0112] Also, a gate line is disposed in a central part of a rectangular pixel area, a storage electrode is formed at an edge of the rectangular pixel area corresponding to a light leakage

blocking part, and a first storage electrode and a second storage electrode are overlapped with each other to adjust an electric capacitance of a storage capacitor, said placement of the storage capacitor parts at the edges thereby preventing aperture ratio from being reduced due to the presence of the storage capacitor. As understood by practitioners, aperture ratio generally refers to the amount of light passed through the display panel when looking at it head-on as compared to the amount of light striking the panel from behind. Use of a black matrix with wide stripes can reduce the aperture ratio. Use of a pixel-electrode with an opaquely obstructed surface area can reduce the aperture ratio. Unlike the actual aperture ratio, the "apparent aperture ratio" may define the amount of image generating efficiency when viewing the display at an angle other than head on. The present disclosure provides for improvements of both the actual aperture ratio and the "apparent" aperture ratio.

[0113] Also, a data line, and first and second storage electrodes are formed to be overlapped with a light leaking area of a pixel electrode, thereby omitting a light intercepting member for an area in which the data line, and the first and second storage electrodes are formed.

[0114] Although a few exemplary embodiments have been shown and described, it will be appreciated by those skilled in the art after reading the present disclosure that changes may be made in these embodiments without departing from the principles and spirit of the disclosure.

1. A method of operating a liquid crystal display (LCD) comprising:

selectively causing liquid crystal material of a same pixel area to twist in opposed directions so as to provide improved image contrasting when the image is viewed from one side or another of the display rather than head on.

2. The method of claim 1 wherein liquid crystal material in a first half of the pixel area is selectively twisted clockwise in response to application of a twisting voltage and liquid crystal material in a second half of the pixel area is selectively twisted counterclockwise in response to said application of the twisting voltage.

3. The method of claim 2 wherein a plurality of pixel areas are arranged as horizontal rows and vertical columns and said first and second halves of the each pixel area are disposed in a corresponding one or another of upper and lower halves of the corresponding row of the pixel area, thereby causing said clockwise and counterclockwise twisting to occur respectively in a corresponding one or another of upper and lower halves of the corresponding row.

4-37. (canceled)

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专利名称(译)	具有反扭曲液晶区域的显示装置及其操作和制造方法		
公开(公告)号	US20100214502A1	公开(公告)日	2010-08-26
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[标]申请(专利权)人(译)	李沧HUN		
申请(专利权)人(译)	李沧HUN		
当前申请(专利权)人(译)	三星DISPLAY CO., LTD.		
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摘要(译)

一种显示装置，包括：第一基板；在第一衬底上形成栅极线；数据线穿过栅极线，并包括源电极；漏电极面向源电极以限定沟道区域；钝化层，形成在数据线和漏电极上，并包括有机材料；像素电极，形成在钝化层上方，并包括第一杆电极，其至少一部分与栅极线或数据线重叠，以及多个第一分支电极，与第一杆电极接触，其中一组第一分支电极在与另一组第一分支电极的纵向延伸方向不同的方向上纵向延伸，从而引起相应的液晶材料的相反扭曲。

